

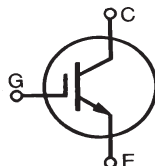
# High Voltage IGBTs

## IXGK100N170 IXGX100N170

$$V_{CES} = 1700V$$

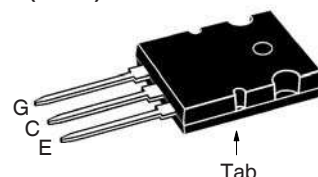
$$I_{C90} = 100A$$

$$V_{CE(sat)} \leq 3.0V$$

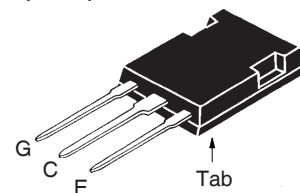


Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ C$ to $150^\circ C$	1700	V
$V_{CGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GE} = 1M\Omega$	1700	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ C$ ( Chip Capability )	170	A
$I_{LRMS}$	Terminal Current Limit	160	A
$I_{C90}$	$T_C = 90^\circ C$	100	A
$I_{CM}$	$T_C = 25^\circ C$ , 1ms	600	A
<b>SSOA</b> <b>(RBSOA)</b>	$V_{GE} = 15V$ , $T_{VJ} = 125^\circ C$ , $R_G = 1\Omega$ Clamped Inductive Load	$I_{CM} = 200$ @ $0.8 \cdot V_{CES}$	A
$t_{sc}$ <b>(SCSOA)</b>	$V_{GE} = 15V$ , $V_{CE} = 1250V$ , $T_J = 125^\circ C$ $R_G = 10\Omega$ , Non Repetitive	10	$\mu s$
$P_C$	$T_C = 25^\circ C$	830	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ C$
$T_{SOLD}$	1.6 mm (0.062in.) from Case for 10s	260	$^\circ C$
$M_d$	Mounting Torque (TO-264)	1.13/10	Nm/lb.in.
$F_C$	Mounting Force (PLUS247)	20..120 / 4.5..27	N/lb.
<b>Weight</b>	TO-264	10	g
	PLUS247	6	g

TO-264 (IXGK)



PLUS247 (IXGX)



G = Gate                      E = Emitter  
C = Collector                Tab = Collector

### Features

- Optimized for Low Conduction and Switching Losses
- Short Circuit Capability
- High Current Handling Capability

### Advantages

- High Power Density
- Low Gate Drive Requirement

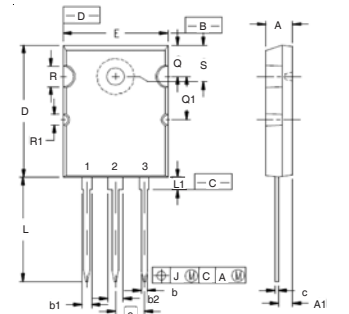
### Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Welding Machines

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{CES}$	$I_C = 3mA$ , $V_{GE} = 0V$	1700		V
$V_{GE(th)}$	$I_C = 8mA$ , $V_{CE} = V_{GE}$	3.0		5.0 V
$I_{CES}$	$V_{CE} = V_{CES}$ , $V_{GE} = 0V$ $T_J = 125^\circ C$			50 $\mu A$ 3 mA
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 200$ nA
$V_{CE(sat)}$	$I_C = 100A$ , $V_{GE} = 15V$ , Note 1		2.5	3.0 V

**Symbol Test Conditions**
 $(T_J = 25^\circ\text{C Unless Otherwise Specified})$ 
**Characteristic Values**

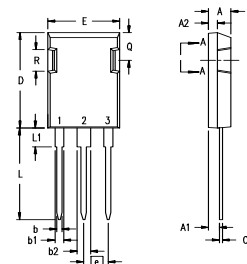
		Min.	Typ.	Max.	
$g_{fs}$	$I_C = 60\text{A}, V_{CE} = 10\text{V}, \text{Note 1}$	36	64		S
$C_{ies}$	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		9200		pF
$C_{oes}$			455		pF
$C_{res}$			150		pF
$Q_g$	$I_C = 100\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		425		nC
$Q_{ge}$			65		nC
$Q_{gc}$			186		nC
$t_{d(on)}$	<b>Resistive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = 100\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 1\Omega$		35		ns
$t_r$			192		ns
$t_{d(off)}$			285		ns
$t_f$			395		ns
$t_{d(on)}$		<b>Resistive load, <math>T_J = 125^\circ\text{C}</math></b> $I_C = 100\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 1\Omega$		35	
$t_r$			250		ns
$t_{d(off)}$			285		ns
$t_f$			435		ns
$R_{thJC}$				0.15	
$R_{thCS}$					$^\circ\text{C/W}$

**TO-264 Outline**


Terminals: 1 = Gate  
2,4 = Collector  
3 = Emitter

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215 BSC		5.46 BSC	
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
$\varnothing P$	.122	.138	3.10	3.51
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
$\varnothing R$	.155	.187	3.94	4.75
$\varnothing R1$	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

Note: 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

**PLUS247™ Outline**


Terminals: 1 - Gate  
2 - Collector  
3 - Emitter

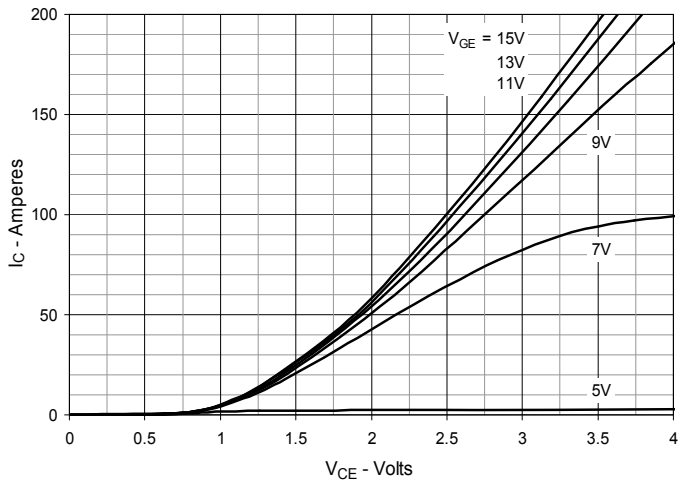
Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A <sub>1</sub>	2.29	2.54	.090	.100
A <sub>2</sub>	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b <sub>1</sub>	1.91	2.13	.075	.084
b <sub>2</sub>	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

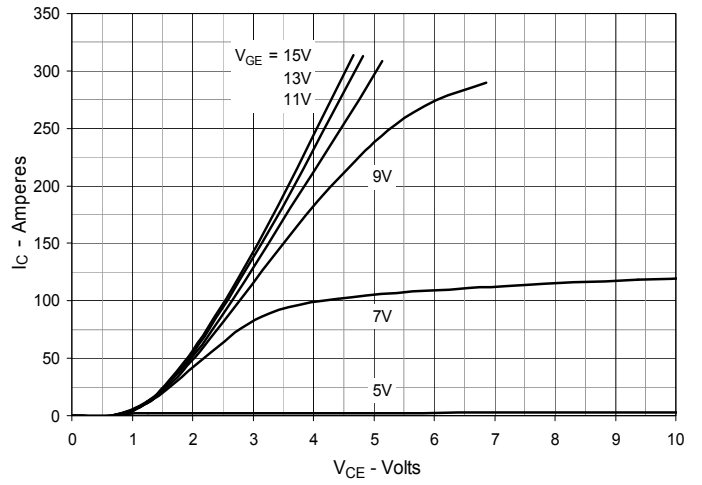
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

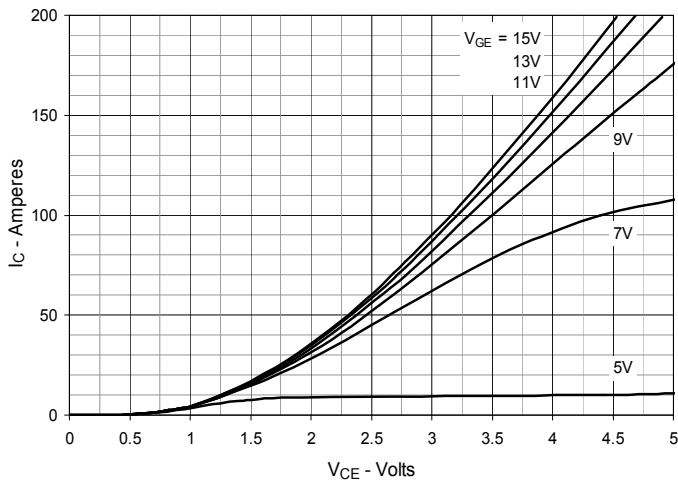
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



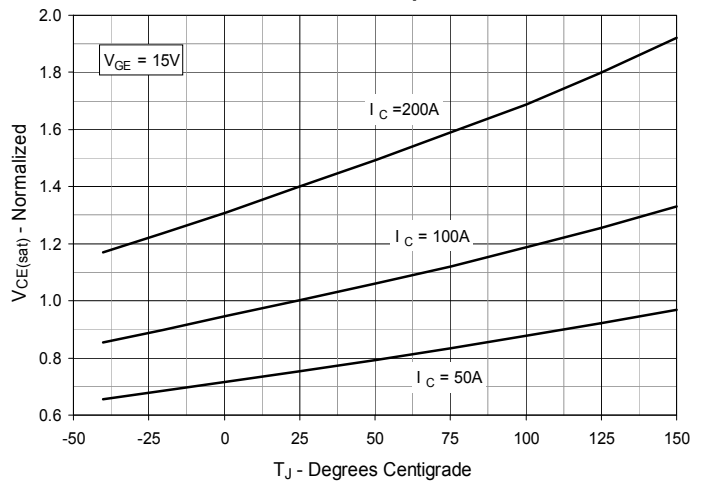
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



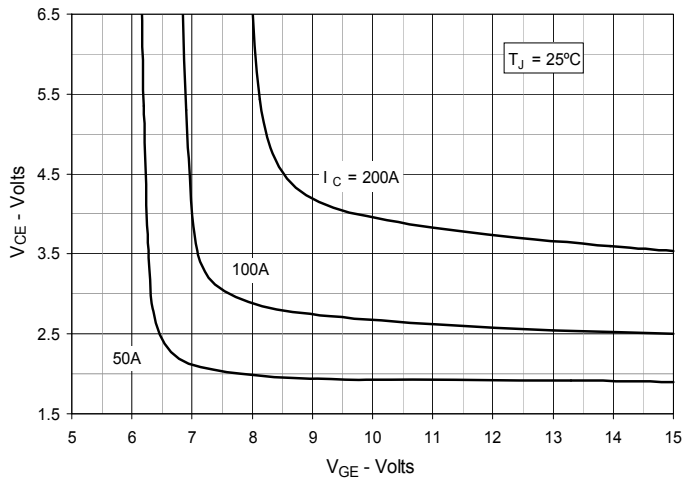
**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$**



**Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature**



**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage**



**Fig. 6. Input Admittance**

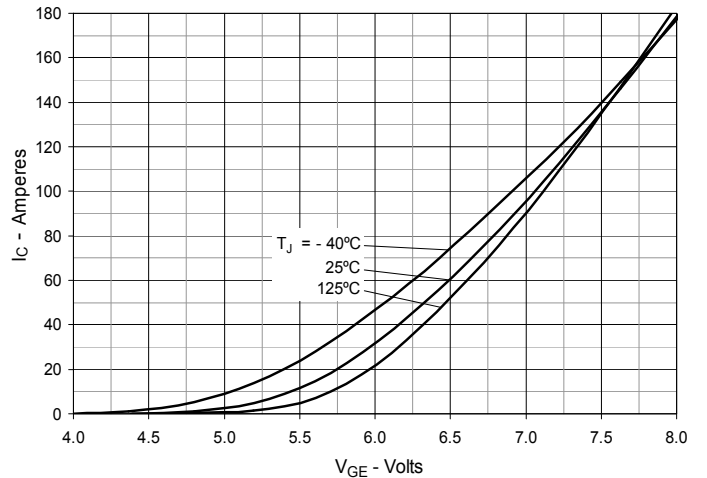


Fig. 7. Transconductance

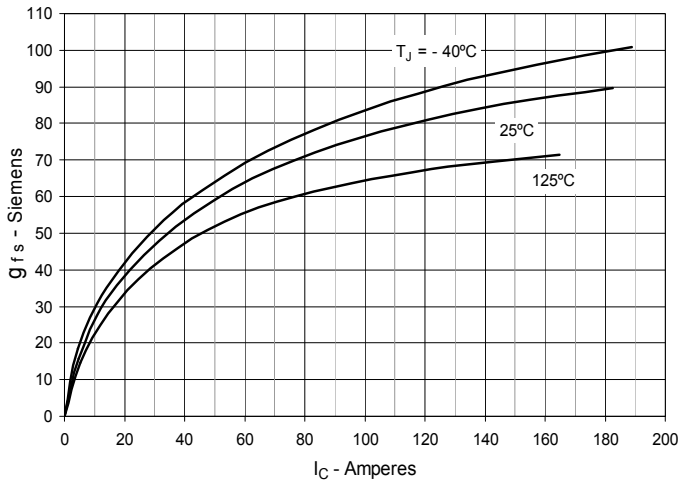


Fig. 8. Gate Charge

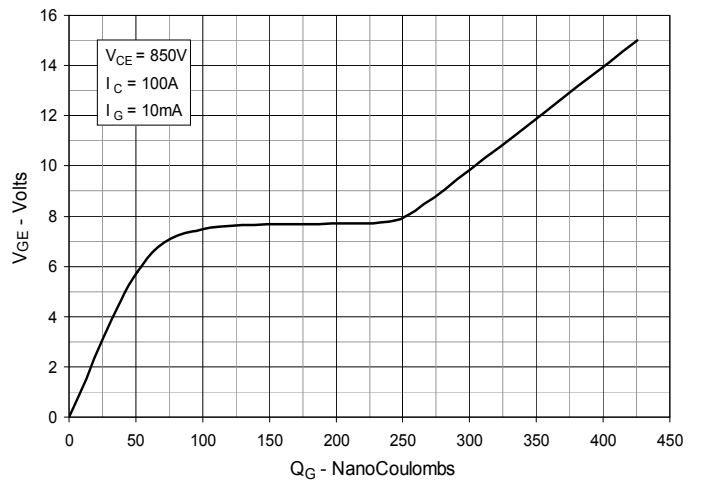


Fig. 9. Reverse-Bias Safe Operating Area

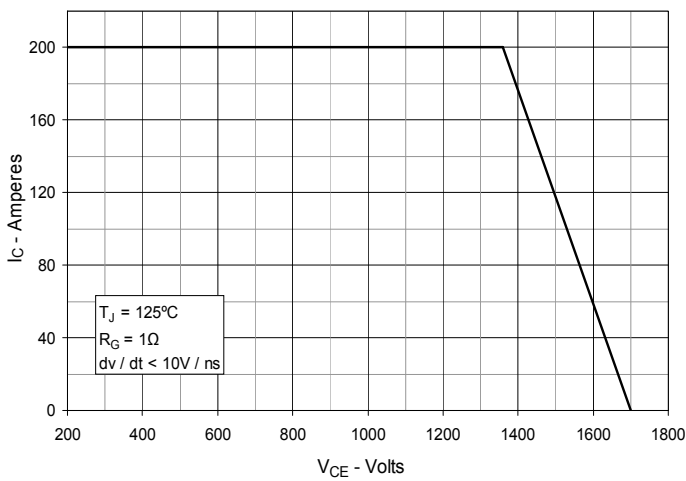


Fig. 10. Capacitance

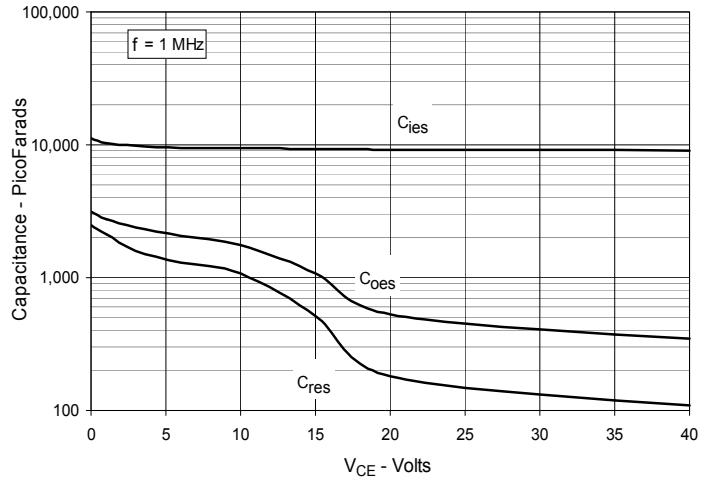
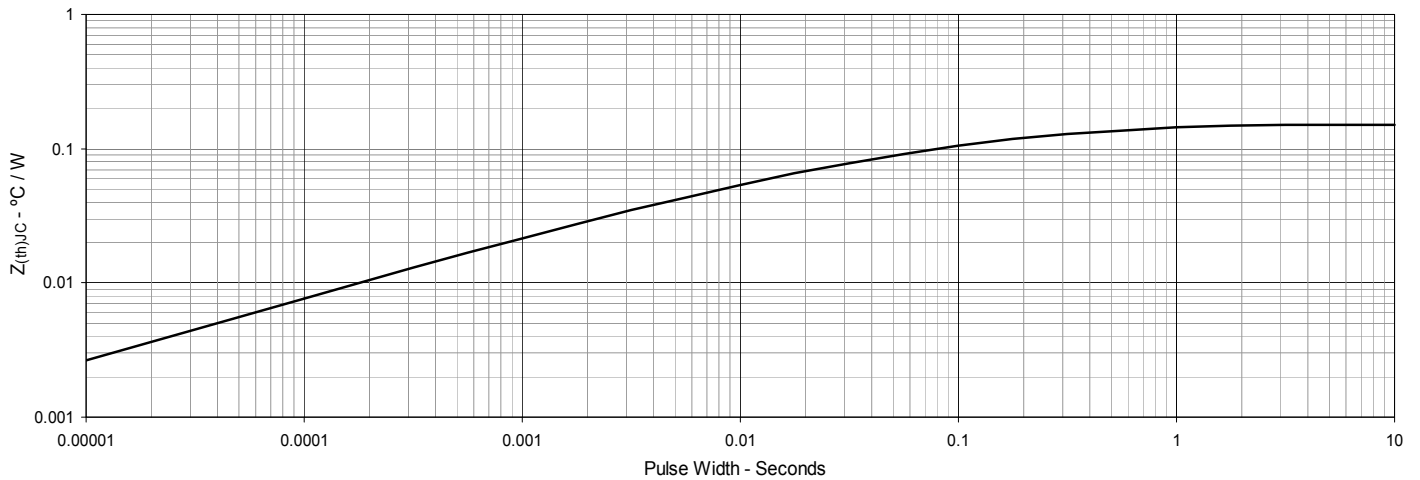
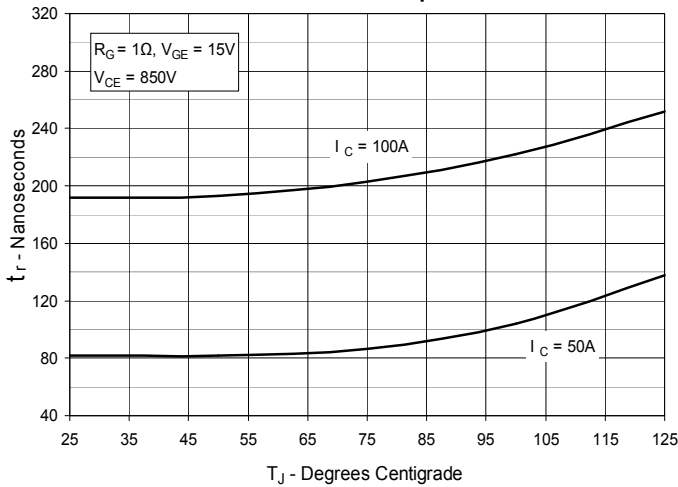


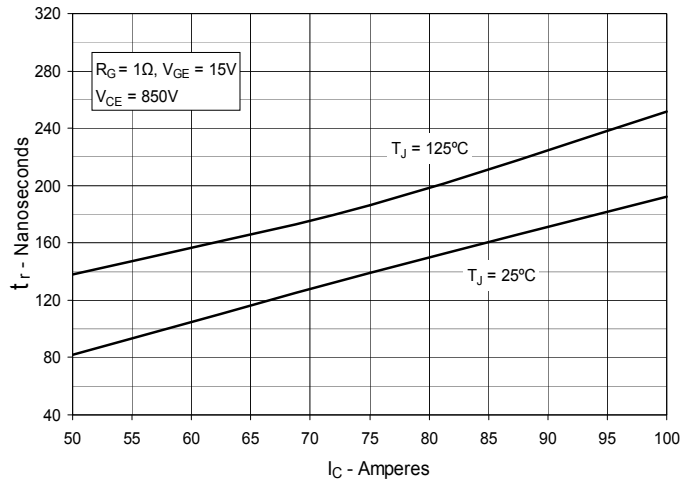
Fig. 11. Maximum Transient Thermal Impedance



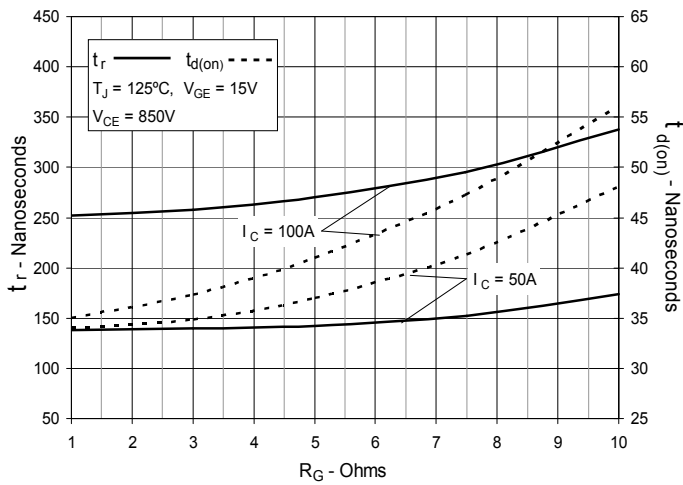
**Fig. 12. Resistive Turn-on Rise Time vs. Junction Temperature**



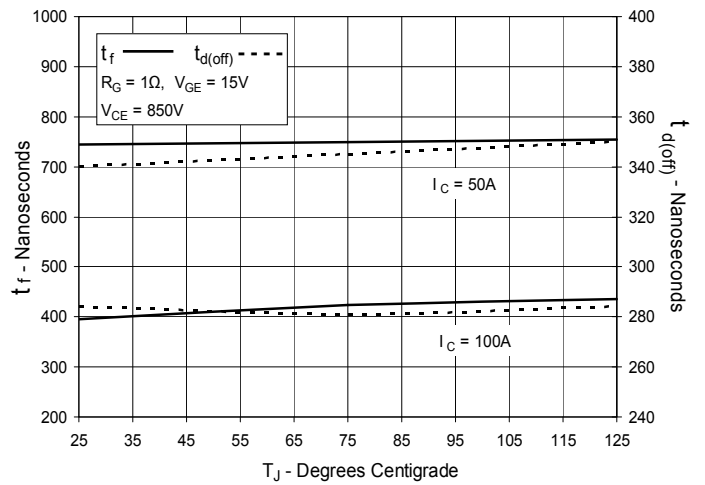
**Fig. 13. Resistive Turn-on Rise Time vs. Collector Current**



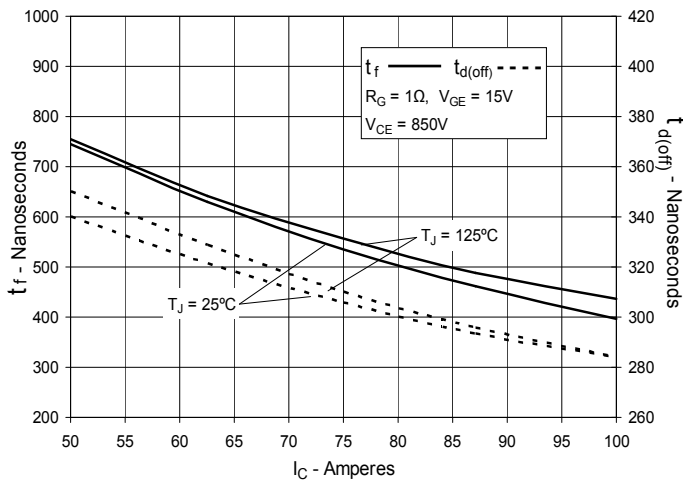
**Fig. 14. Resistive Turn-on Switching Times vs. Gate Resistance**



**Fig. 15. Resistive Turn-off Switching Times vs. Junction Temperature**



**Fig. 16. Resistive Turn-off Switching Times vs. Collector Current**



**Fig. 17. Resistive Turn-off Switching Times vs. Gate Resistance**

